

Features :

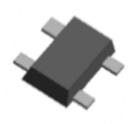
 Low noise figure and high associated gain NF=0.4dB Typ., Ga=17.0dB Typ.
@Vdd=3.0V, Idd=15mA, f=1.575GHz

Applications :

- Low Noise Amplifier IC for Global Navigation Satellite Systems (GNSS) like GPS, GLONASS, Beidou and Galileo
- Low Noise Amplifier IC for Satellite Radio (SDARS, DMB, etc.) Antenna
- Low Noise Amplifier for Microwave Communication

Description :

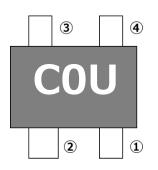
- Low Noise and High Gain
- On chip Bias supply circuit
- On chip ESD protection diode



Package :

 Flat-lead 4-pin thin-type super minimold package

PIN Configuration :



PIN No.	PIN Name
1	Source
2	OUT
3	Source
4	IN

Ordering Information :

Part Number	Order Number	Package	Marking	Supplying Form
CA3509M4	CA3509M4-C2B	Flat-lead 4-pin	COU	•Embossed 8 mm wide
		thin-type super		•Pin 1 (Source), Pin 2 (OUT)
		minimold package		Face the perforation side of the
				Таре
				•Qty 5Kpcs/reel



L TO S BAND LOW NOISE AMPLIFIER IC

Absolute Maximum Ratings :

Parameter	Symbol	Rating	Unit
Supply Voltage	Vdd	4.0	V
RF Input Power	PRFin	+13	dBm
Operating Ambient Temperature	T _A	-45~+85	°C
Storage Temperature	Tstg	-55~+150	°C

Recommended Operating Range :

 $(T_A=+25^{\circ}C, \text{ unless otherwise specified})$

Parameter	Symbol	MIN.	TYP.	MAX.	Unit
Supply Voltage	Vdd	2.7	3.0	3.3	V
Supply Current	Idd	11.4	15	20.6	mA

Electrical Characteristics:

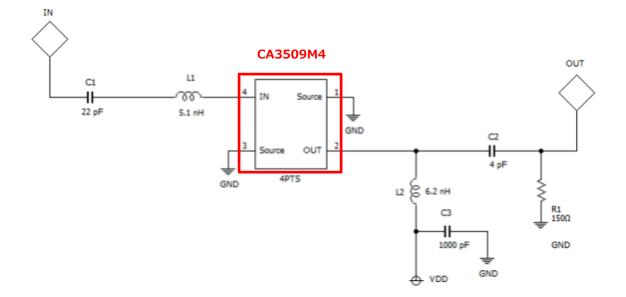
 $(T_A = +25^{\circ}C, \text{ unless otherwise specified}) *With Matching Circuit$

Parameter	Symbol	Condition	MIN.	TYP.	MAX.	Unit
Power Gain	Gain	Vdd=3.0V, Idd=15mA,	15.5	17.0	-	dB
Noise Figure	NF	f=1.575GHz	-	0.40	0.65	dB
Input 3rd Order Intercept Point	IIP3	Vdd=3.0V, Id=15mA, f=1.575GHz	-	+4.5	-	dBm
Output Power at 1dB Compression Point	P _{O(1dB)}	Vdd=3.0V, Idd=15mA (Non-RF) f=1.575GHz	-	12.0	_	dBm

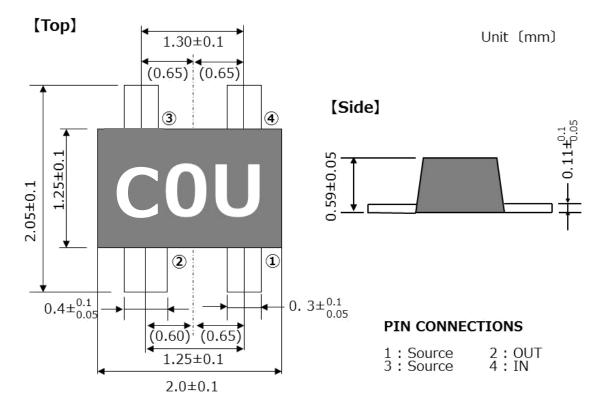


DATA SHEET: CA3509M4 L TO S BAND LOW NOISE AMPLIFIER IC

Application Circuit:



Package Dimensions :







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L TO S BAND LOW NOISE AMPLIFIER IC

[Caution in the gallium arsenide (GaAs) product handling]

This product uses gallium arsenide (GaAs) of the toxic substance appointed in laws and ordinances. GaAs vapor and powder are hazardous to human health if inhaled or ingested.

- Do not dispose in fire or break up this product.
- \cdot Do not chemically make gas or powder with this product.
- \cdot When discard this product, please obey the law of your country.
- \cdot Do not lick the product or in any way allow it to enter the mouth.

[CAUTION]

Although this device is designed to be as robust as possible, ESD (Electrostatic Discharge) can damage this device. This device must be protected at all times from ESD. Static charges may easily produce potentials of several kilovolts on the human body or equipment, which can discharge without detection. Industry-standard ESD precautions should be used at all times.

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Please visit our website: www.cel.com/contactus

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DATA SHEET: CA3509M4

L TO S BAND LOW NOISE AMPLIFIER IC

Revision History

Version	Changes to current version	Page(s)
CDS-0043-01	Preliminary data sheet	N/A
Jan 2018		
CDS-0043-02	Revised Supply Voltage	1, 2, 3
March 2018	Revised Application Circuit	3
CDS-0043-02	Changed part number from CE3509M4 to CA3509M4	All
June 2018		
	•Revised RF Input Power from +15 to +13 dBm	1, 2
CDS-0043-03	Revised Supply Voltage from 2.85V to 3.0V	1, 2
Aug 2018	•Revised Output Power at 1dB Compression Point from 11 to 12dBm	2
	Changed Application Circuit	3
CDS-0043-03a	Changed marking information	1, 3
Dec 2018		
CDS-0043-05	Removed "Preliminary"	All
March 2019	Updated part number and reel size	1
	Updated Electrical Characteristics tables	2
CDS-0043-06	Revised Max Supply Current (from 20.2mA to 20.6mA)	2
May 2019		